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SEMICONDUCTOR TECHNOLOGIES LLC

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CLERK U.S. DISTRICT COURT
CENTRAL DIST. OF CALIF.
LOS ANGELES

UNITED STATES DISTRICT COURT
CENTRAL DISTRICT OF CALIFORNIA

SEMICONDUCTOR TECHNOLOGIES
LLC,

Plaintiff,

vs.

HYNIX SEMICONDUCTOR
AMERICA INC.;
HYNIX SEMICONDUCTOR
MANUFACTURING AMERICA INC.;
AND
HYNIX SEMICONDUCTOR INC.;

Defendants.

Case No.: _____

SACV11-1788 JSI (RNPX)

**ORIGINAL COMPLAINT FOR
PATENT INFRINGEMENT**

JURY TRIAL DEMANDED

Filing Date: TBD

Trial Date: TBD

Discovery Cut-off: TBD

Motion Cut-off: TBD

This is an action for patent infringement in which Semiconductor Technologies LLC submits this Original Complaint against Hynix Semiconductor America Inc.; Hynix Semiconductor Manufacturing America Inc.; and Hynix Semiconductor Inc.

PARTIES

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2 1. Semiconductor Technologies LLC ("STL" or "Plaintiff") is a California
3 limited liability company with a place of business at 500 Newport Center Drive,
4 Suite 700, Newport Beach, CA 92660.

6 2. On information and belief, Hynix Semiconductor America Inc. ("Hynix
7 America") is a California corporation with a place of business at 3101 North First
8 Street, San Jose, California 95134.

10 3. On information and belief, Hynix Semiconductor Manufacturing
11 America Inc. ("Hynix Manufacturing") is a California corporation with a place of
12 business at 1830 Willow Creek Circle, Eugene, Oregon 97402.

14 4. On information and belief, Hynix Semiconductor Inc. ("Hynix Korea") is
15 an entity organized under the laws of a Korea with a place of business at San 136-1,
16 Ami-Ri Bubaleub Ichon-si Kyoungki-do, South Korea 467-860. Hynix America,
17 Hynix Manufacturing and Hynix Korea are referred to collectively as "Defendants" or
18 "Hynix."

JURISDICTION AND VENUE

22 5. This action arises under the patent laws of the United States, Title 35 of
23 the United States Code. This Court has subject matter jurisdiction pursuant to
24 28 U.S.C. §§ 1331 and 1338(a). On information and belief, Defendants are subject to
25 this Court's specific and general personal jurisdiction, pursuant to due process and/or
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1 the California Long Arm Statute, due at least to their substantial business in this
2 forum, including at least a portion of the infringements alleged herein. On
3 information and belief, within this district Defendants, directly and/or through
4 intermediaries, have advertised (including through websites), offered to sell, sold
5 and/or distributed infringing products, and/or have induced the sale and use of
6 infringing products. Further, on information and belief, Defendants are subject to the
7 Court's general jurisdiction, including from regularly doing or soliciting business,
8 engaging in other persistent courses of conduct, and/or deriving substantial revenue
9 from goods and services provided to individuals in California.

13 6. Venue is proper in this district under 28 U.S.C. §§ 1391(b), 1391(c) and
14 1400(b). On information and belief, from and within this Judicial District each
15 Defendant has committed at least a portion of the infringements at issue in this case.
16 Without limitation, on information and belief, within this district Defendants, directly
17 and/or through intermediaries, have advertised (including through websites), offered
18 to sell, sold and/or distributed infringing products, and/or have induced the sale and
19 use of infringing products.

23 **COUNT I**

24 **INFRINGEMENT OF U.S. PATENT NO. 6,828,242**

1 7. STL is the exclusive licensee of United States Patent No. 6,828,242
2 (“the ‘242 patent”), entitled “Method for Manufacturing Semiconductor Integrated
3 Circuit Device.” The ‘242 patent was duly and legally issued on December 7, 2004.
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5 8. As exclusive licensee, STL holds all substantial rights in and to
6 the ‘242 patent, including, without limitation, the exclusive right to grant sublicenses,
7 to sue for and collect past, present and future damages, and the exclusive right to seek
8 and obtain injunctive relief or any other relief for infringement of the ‘242 patent.
9 Accordingly, STL has standing to bring this lawsuit for infringement of the ‘242
10 patent.
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12 9. On information and belief, Hynix has infringed the ‘242 patent by actions
13 comprising making and using the methods claimed in the ‘242 patent in the
14 manufacture of semiconductor integrated circuit devices, including DRAM chips such
15 as the Hynix H5TQ1G83BFR 54nm 1G DDR3 SDRAM and similar chips, including
16 practicing the steps of (a) forming a silicon film over a semiconductor substrate via a
17 first insulating film; (b) forming a refractory metal film on the silicon film; (c)
18 forming a second insulating film on the refractory metal film; (d) processing the
19 second insulating film into a predetermined shape; (e) etching the refractory metal
20 film and a predetermined thickness of a part of the silicon film where it is not covered
21 with the predetermined shaped second insulating film so as not to expose the first
22 insulating film; (f) selectively forming a third insulating film on a sidewall of the
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1 silicon film left below the refractory metal film, on sidewalls of the refractory metal
2 film and on sidewalls of the second insulating film; (g) removing a part of the silicon
3 film not covered with the third insulating film; and (h) performing a thermal treatment
4 to a surface of the silicon film in an oxidation atmosphere, thus forming a fourth
5 insulating film in a sidewall of the silicon film by oxidizing a side surface of the
6 silicon film.
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9 10. On information and belief, Hynix has been and now is infringing
10 the '242 patent by actions comprising importing into the United States and offering to
11 sell, selling and using within the United States, during the term of the '242 patent,
12 products, including DRAM chips such as the Hynix H5TQ1G83BFR 54nm 1G DDR3
13 SDRAM and similar chips, which are made by the foregoing processes claimed in
14 the '242 patent.
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17 11. Accordingly, on information and belief, Hynix is liable for infringement
18 of the '242 patent.
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20 **COUNT II**

21 **INFRINGEMENT OF U.S. PATENT NO. 7,224,034**

22 12. STL is the exclusive licensee of United States Patent No. 7,224,034
23 ("the '034 patent"), entitled "Method for Manufacturing Semiconductor Integrated
24 Circuit Device." The '034 patent was duly and legally issued on May 29, 2007.
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1 13. As exclusive licensee, STL holds all substantial rights in and to
2 the '034 patent, including, without limitation, the exclusive right to grant sublicenses,
3 to sue for and collect past, present and future damages, and the exclusive right to seek
4 and obtain injunctive relief or any other relief for infringement of the '034 patent.
5 Accordingly, STL has standing to bring this lawsuit for infringement of
6 the '034 patent.
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9 14. On information and belief, Hynix has been and now is infringing
10 the '034 patent by actions comprising making, using, selling, offering for sale and/or
11 importing semiconductor integrated circuit devices, including DRAM chips such as
12 the Hynix H5TQ1G83BFR 54nm 1G DDR3 SDRAM and similar chips, that comprise
13 (a) a semiconductor substrate having a main surface; (b) a first insulating film formed
14 on the main surface of the semiconductor substrate; (c) a silicon film formed on the
15 first insulating film, which has a first sidewall positioned adjacent to the first
16 insulating film and a second sidewall positioned apart from the first insulating film;
17 (d) a refractory metal film formed above the silicon film and having a third sidewall;
18 (e) a second insulating film formed on the second and third sidewalls; and (f) a third
19 insulating film formed on the first sidewall, wherein the third insulating film has a
20 first portion positioned between the first and second insulating films and a second
21 portion positioned between the first portion and the silicon film, wherein an upper end
22 of the second portion of the third insulating film is higher than that of the first portion
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